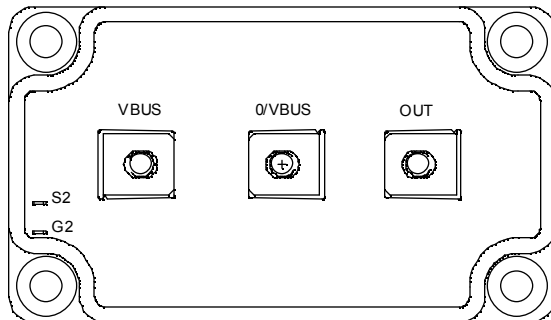
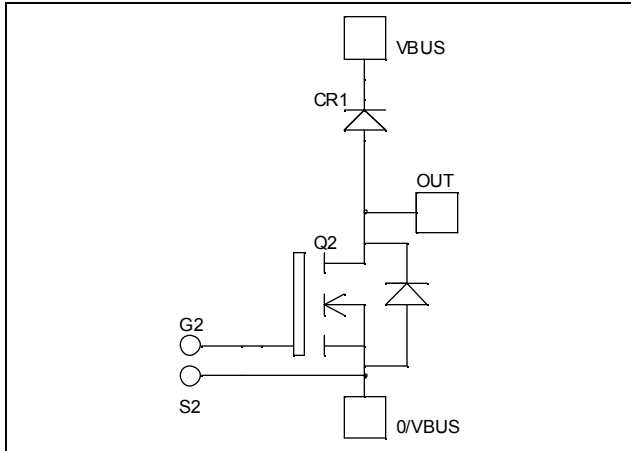


Boost chopper MOSFET Power Module

$V_{DSS} = 500V$

$R_{DSon} = 19m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 163A$ @ $T_c = 25^\circ C$



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	163
		$T_c = 80^\circ C$	122
I_{DM}	Pulsed Drain current	652	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	22.5	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	1136
I_{AR}	Avalanche current (repetitive and non repetitive)	46	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	2500	



These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			200	μA
		$V_{GS} = 0V, V_{DS} = 400V$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 81.5A$		19	22.5	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10mA$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		22.4		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		4.8		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.36		
Q_g	Total gate Charge	$V_{GS} = 10V$		492		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250V$		132		
Q_{gd}	Gate – Drain Charge	$I_D = 163A$		260		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 163A$ $R_G = 1\Omega$		18		ns
T_r	Rise Time			35		
$T_{d(off)}$	Turn-off Delay Time			87		
T_f	Fall Time			77		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 163A, R_G = 1\Omega$		3020		μJ
E_{off}	Turn-off Switching Energy			2904		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 163A, R_G = 1\Omega$		4964		μJ
E_{off}	Turn-off Switching Energy			3384		

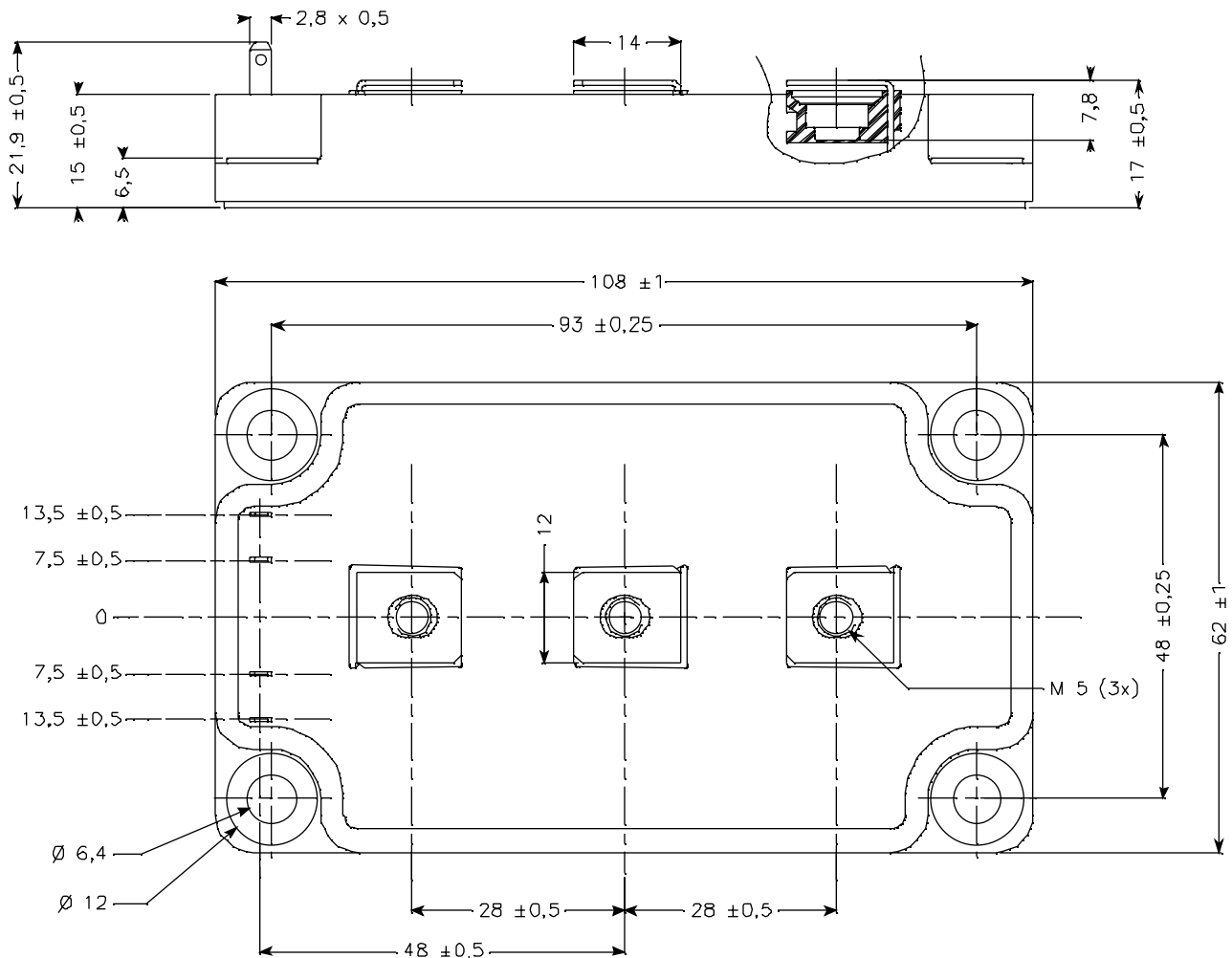
Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C			350	μA
			T _j = 125°C			600	
I _F	DC Forward Current		T _c = 70°C		120		A
V _F	Diode Forward Voltage	I _F = 120A			1.6	1.8	V
		I _F = 240A			1.9		
		I _F = 120A	T _j = 125°C		1.4		
t _{rr}	Reverse Recovery Time	I _F = 120A V _R = 400V di/dt = 400A/μs	T _j = 25°C		130		ns
	T _j = 125°C			170			
Q _{rr}	Reverse Recovery Charge			T _j = 25°C		440	
			T _j = 125°C		1840		

Thermal and package characteristics

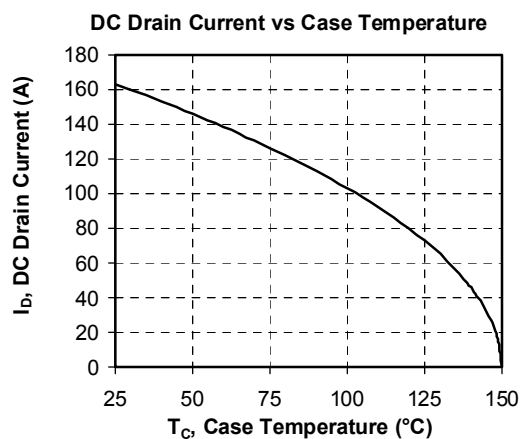
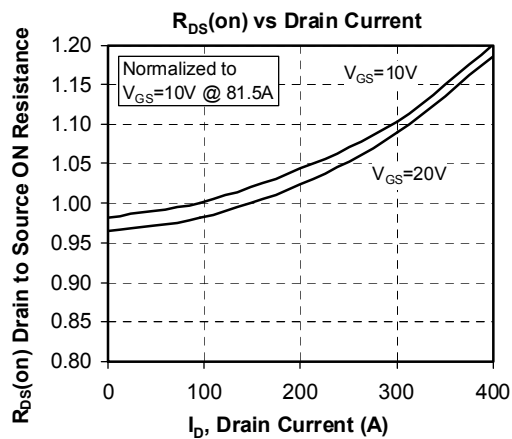
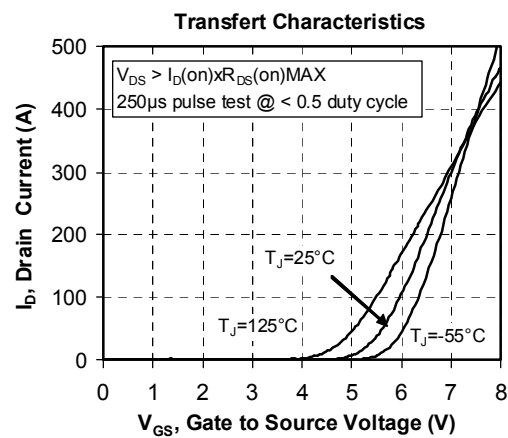
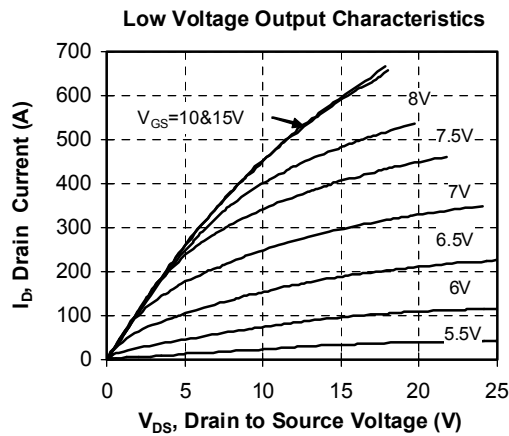
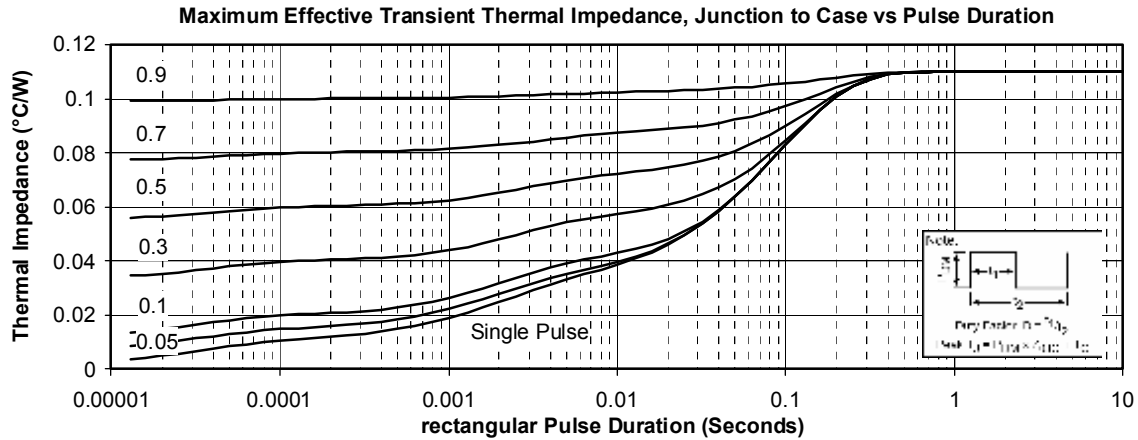
Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance			Transistor		0.11	°C/W
				Diode		0.46	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					280	g

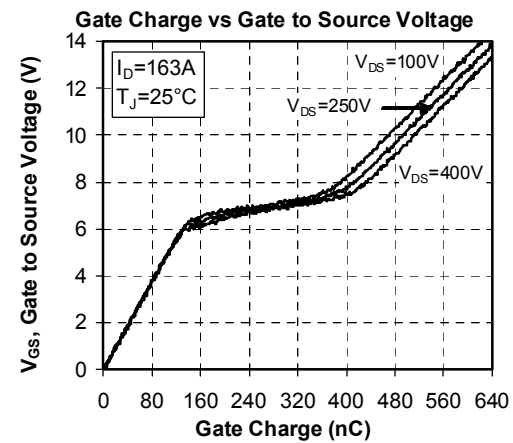
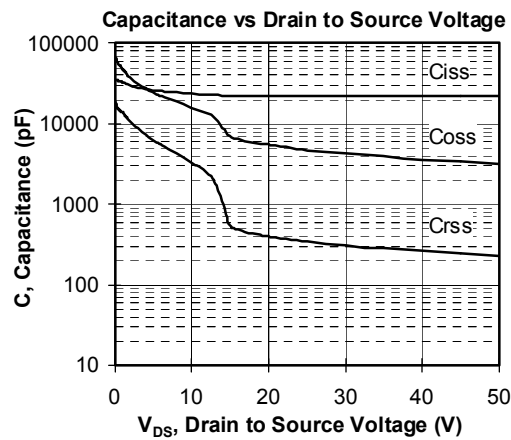
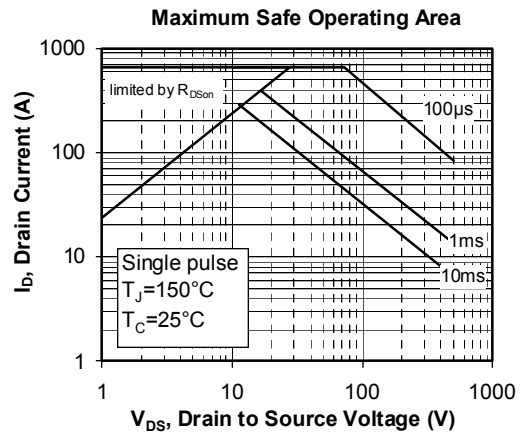
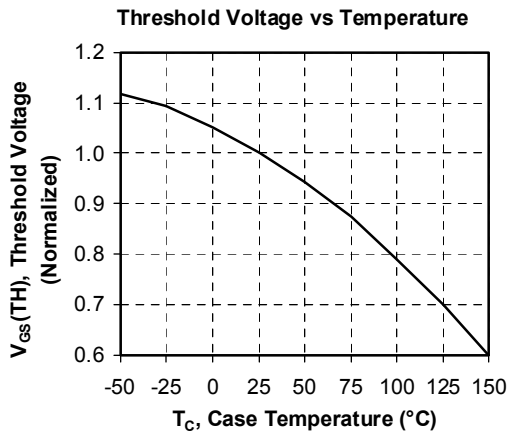
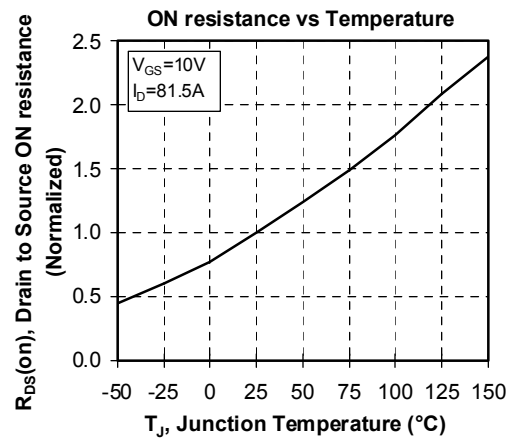
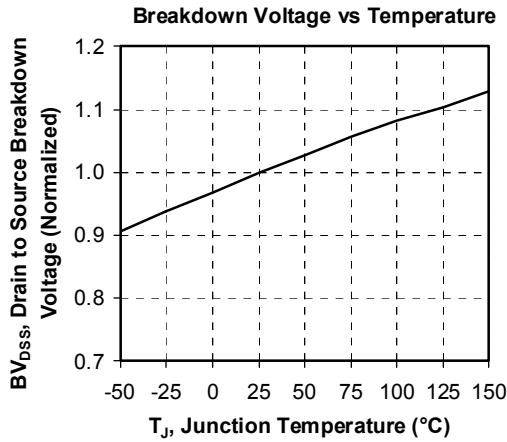
SP6 Package outline (dimensions in mm)

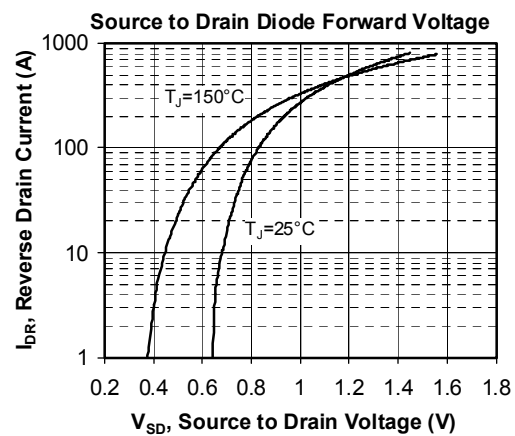
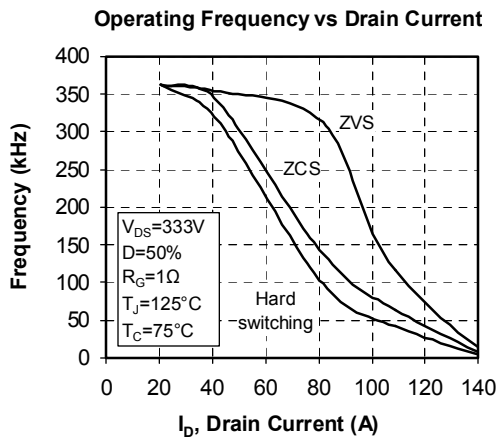
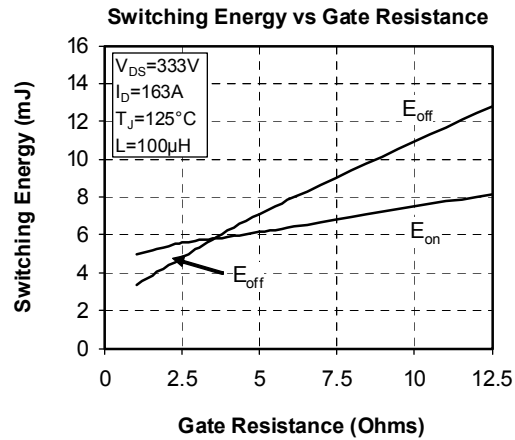
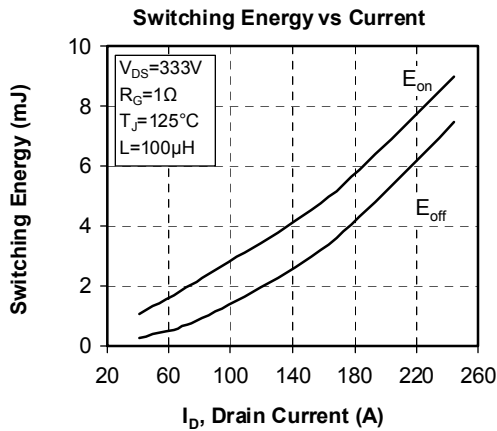
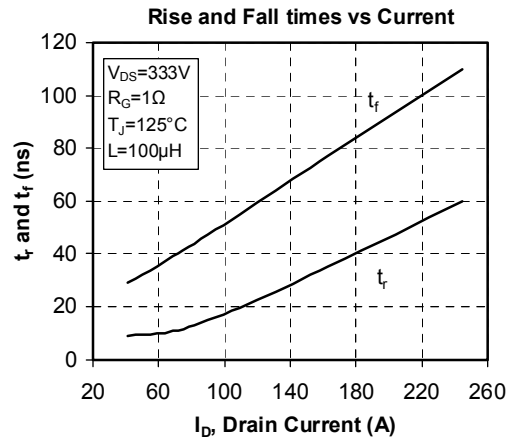
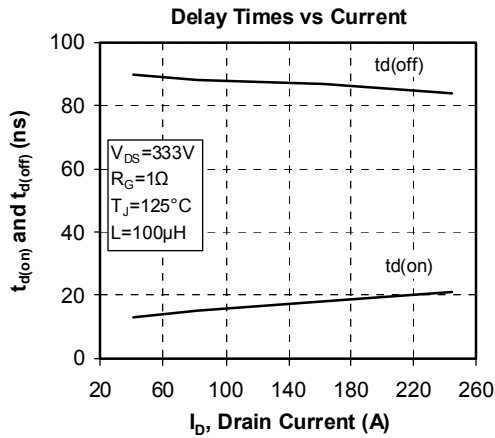


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve







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